

ABSTRACT OF THE DISCLOSURE

A nonvolatile semiconductor memory device that can be miniaturized is provided. A method of manufacturing the nonvolatile semiconductor memory device includes the steps of: forming an interlayer insulating film covering a stacked structure and a sidewall insulating film and having a top surface approximately parallel to a main surface; forming a resist pattern as a mask layer on the top surface of the interlayer insulating film; forming a groove as an opening in the interlayer insulating film to be positioned between the sidewall insulating films formed at the adjacent stacked structures; and forming a source region extending along a plurality of floating gate electrodes by implanting impurity ions from the groove to the main surface.